



1200V, 100A, Trench FS II Fast IGBT

General Description:

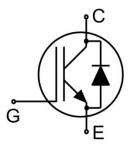
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 1200V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- Trench FSII Technology Offering
- Very low V_{CE(sat)}
- High speed switching
- Positive temperature coefficient in V_{CE(sat)}
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- PV power
- Three-level Solar String Inverter



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking		
NCE100TD120VTP	TO-247P	NCE100TD120VTP		

TO-247P

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate- Emitter Voltage	±20	V
I.	Collector Current	400	А
Ic	Collector Current @T _C = 100 °C	100	А
I _{Cpuls}	Pulsed Collector Current, t _p limited by T _{jmax}	300	А
-	turn off safe operating area,V _{CE} =1200V,Tj=150°C	300	А
	Diode Continuous Forward Current @T _C = 25 °C	200	
l _F	Diode Continuous Forward Current @T _C = 100 °C	100	А
I _{FM}	Diode Maximum Forward Current	400	А
Ъ	Power Dissipation @ T _C = 25°C	1071	W
P _D	Power Dissipation @T _C = 100 °C	535.5	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +175	°C
T∟	Maximum Temperature for Soldering	260	°C



NCE100TD120VTP

Thermal Characteristic

Symbol	Parameter	Value	Units
R ₀ JC	Thermal Resistance, Junction to case for IGBT	0.14	°C/W
R ₀ JC	Thermal Resistance, Junction to case for Diode	0.30	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	40	°C/W

Electrical Characteristics (T_C=25°C unless otherwise noted)

0		Parameter Test Conditions		Value			
Symbol	Parameter			Min.	Тур.	Max.	Units
Static Chara	cteristics	•					
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V	,I _{CE} =1mA	1200			V
I _{CES}	Collector-Emitter Leakage Current	V _{GE} =0V,\	/ _{CE} =1200V			8	uA
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+30	V,V _{CE} =0V			200	nA
I _{GES(R)}	Gate to Source Reverse Leakage	V _{GE} =-30	/,V _{CE} =0V			200	nA
	Callegater Fraitter Cationation Voltage	I _C =100A	Tj=25°C		1.75	1.95	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V _{GE} =15V	Tj=150°C		1.95		V
$V_{\text{GE(th)}}$	Gate Threshold Voltage	I _C =1mA,V _{CE} =V _{GE}		5.0		6.5	V
Dynamic Cha	aracteristics						
Cies	Input Capacitance	V _{CE} =30V,V _{GE} =0V, f=1MHz			12670		pF
Coes	Output Capacitance				425		
Cres	Reverse Transfer Capacitance				352		
Qg	Total Gate Charge	V _{CC} =960V, I _C =100A, V _{GE} =15V			743		nC
Q _{ge}	Gate to Emitter Charge				89		
Q_{gc}	Gate to Collector Charge	_ VGE	A A GE - 13A		478		
Switching Cl	haracteristics	·					
t _{d(ON)}	Turn-on Delay Time				19		
t _r	Rise Time				17		
t _{d(OFF)}	Turn-Off Delay Time	$V_{CE}=600V,I_{C}=100A,$ $V_{GE}=0/15V, R_{g}=8\Omega$			170		ns
t _f	Fall Time				18		
Eon	Turn-On Switching Loss	Inducti	ve Load		8.2		
E _{off}	Turn-Off Switching Loss				3.7		mJ
E _{ts}	Total Switching Loss				11.9		

Electrical Characteristics of the Diode(T_C = 25°C unless otherwise specified):

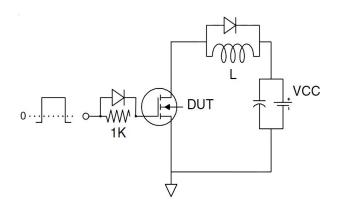
Symbol	Parameter	Test Conditions	Rating			Heite
			Min.	Тур.	Max.	Units
V _{FM}	Diode Forward Voltage	I _F =100A		2.2	3.0	V
T _{rr}	Reverse Recovery Time	1 -504		190		ns
I _{RRM}	Diode Peak Reverse Recovery Current	l _F =50A, di/dt=950A/us		30		Α
Qrr	Reverse Recovery Charge	ui/ui-950A/us		5.4		uC
Pulse width t _{tp} ≤380μs,δ≤2%						

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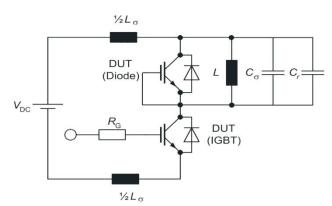


Test Circuit

1) Gate Charge Test Circuit

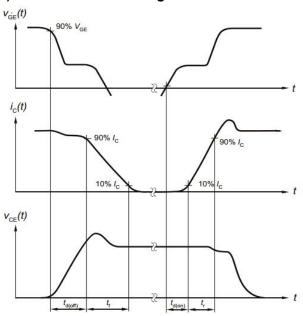


2) Switch Time Test Circuit

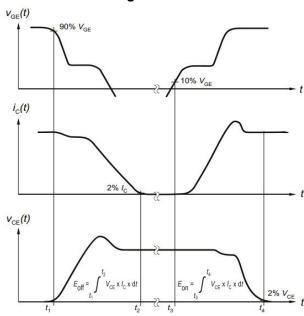


Switching characteristics

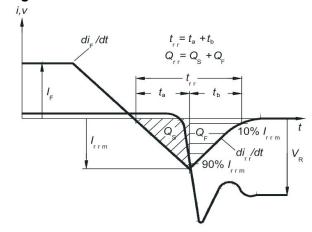
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics





Typical Electrical and Thermal Characteristics



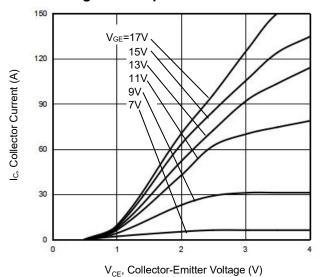


Figure 3 V_{CE(sat)} vs. Case Temperature

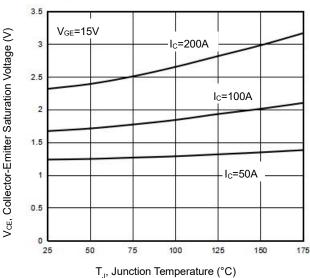
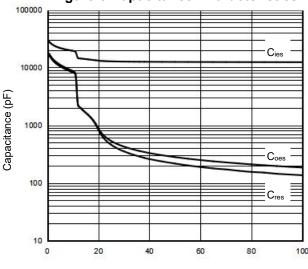


Figure 5 Capacitance Characteristics



V_{CE}, Collector-Emitter Voltage (V)

Figure 2 Transfer Characteristics

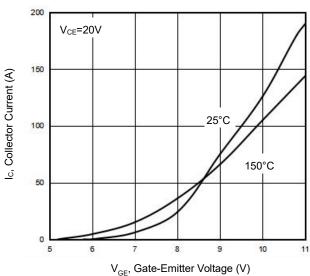


Figure 4 Saturation Voltage vs. V_{GE}

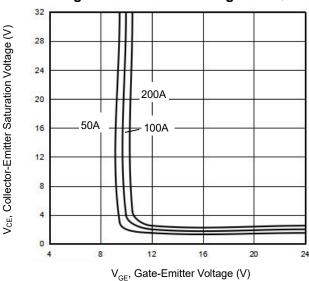
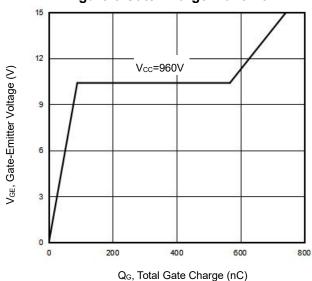


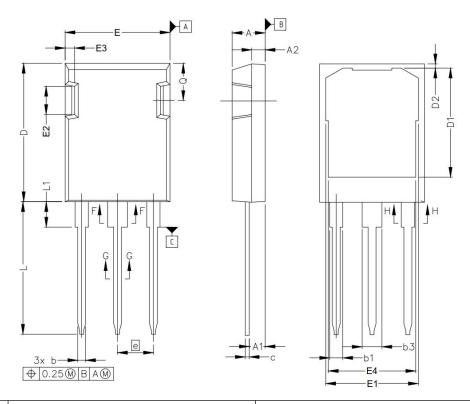
Figure 6 Gate Charge Wave Form





NCE100TD120VTP

TO-247P Package Information



Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	4.83	5.21	0.19	0.21	
A1	2.29	2.54	0.09	0.10	
A2	1.91	2.16	0.08	0.09	
b	1.07	1.33	0.04	0.05	
b1	1.91	2.41	0.08	0.09	
b3	2.87	3.38	0.11	0.13	
С	0.55	0.68	0.02	0.03	
D	20.80	21.10	0.82	0.83	
D1	16.25	17.65	0.64	0.69	
D2	0.50	0.80	0.02	0.03	
E	15.75	16.13	0.62	0.64	
E1	13.10	14.15	0.52	0.56	
E2	3.68	5.10	0.14	0.20	
E3	1.00	1.90	0.04	0.07	
E4	12.38	13.43	0.49	0.53	
е	5.44BSC		0.21		
N	3.00		0.1	12	
L	19.81	20.32	0.78 0.80		
L1	3.70	4.00	0.15	0.16	
Q	5.49	6.00	0.22	0.24	

NCE100TD120VTP

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